

N-Channel Power MOSFET

60V, 300mA, 2Ω

FEATURES

- Low On-Resistance
- ESD Protected 2KV
- High Speed Switching
- Low Voltage Drive

| KEY PERFORMANCE PARAMETERS | | | | |
|----------------------------|-----------------------|-------|------|--|
| PARAMETER | | VALUE | UNIT | |
| $V_{	extsf{DS}}$ | | 60 | V | |
| R _{DS(on)} (max) | V _{GS} = 10V | 2 | | |
| | $V_{GS} = 4.5V$ | 4 | Ω | |
| Q_g | | 0.4 | nC | |

APPLICATION

- Logic Level translators
- DC-DC Converter

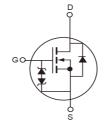






SOT-23





Notes: Moisture sensitivity level: level 3. Per J-STD-020

| ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted) | | | | | |
|---|---------------------|-------------------|--------------|------|--|
| PARAMETER | | SYMBOL | LIMIT | UNIT | |
| Drain-Source Voltage | | V_{DS} | 60 | V | |
| Gate-Source Voltage | | V_{GS} | ±20 | V | |
| Continuous Drain Current (Note 1) | $T_A = 25^{\circ}C$ | I _D | 300 | A | |
| Continuous Drain Current | $T_A = 100$ °C | | 180 | mA | |
| Pulsed Drain Current (Note 2) | | I _{DM} | 800 | mA | |
| Total Power Dissipation @ T _A = 25°C | | P _{DTOT} | 300 | mW | |
| Single Pulsed Avalanche Energy (Note 3) | | E _{AS} | 0.2 | mJ | |
| Single Pulsed Avalanche Current (Note 3) | | I _{AS} | 2 | А | |
| Operating Junction and Storage Temperature Range | | T_J,T_STG | - 55 to +150 | °C | |

| THERMAL PERFORMANCE | | | | |
|--|-----------------|-------|------|--|
| PARAMETER | SYMBOL | LIMIT | UNIT | |
| Junction to Ambient Thermal Resistance | $R_{\Theta JA}$ | 350 | °C/W | |

Notes: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air



| PARAMETER | CONDITIONS | SYMBOL | MIN | TYP | MAX | UNIT |
|----------------------------------|---|---------------------|--------|-----|-------|------|
| Static (Note 4) | CONDITIONS | STINIBOL | 141114 | 116 | IIIAA | ONIT |
| Drain-Source Breakdown Voltage | $V_{GS} = 0V, I_{D} = 10\mu A$ | BV _{DSS} | 60 | | | V |
| Gate Threshold Voltage | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$ | V _{GS(TH)} | 1.0 | 1.5 | 2.5 | V |
| Gate Body Leakage | $V_{GS} = \pm 20V, V_{DS} = 0V$ | I _{GSS} | | | ±10 | μA |
| Zero Gate Voltage Drain Current | V _{DS} =60V, V _{GS} =0V | I _{DSS} | | | 1.0 | μA |
| Drain-Source On-State Resistance | $V_{GS} = 10V, I_D = 300mA$ | | | 1.2 | 2 | mΩ |
| | V _{GS} =4.5V, I _D =200mA | R _{DS(ON)} | | 2 | 4 | |
| Forward Transconductance | V _{DS} =10V, I _D =200mA | g _{fs} | 100 | | | mS |
| Diode Forward Voltage | I _S =300mA, V _{GS} =0V | V _{SD} | | 0.8 | 1.4 | V |
| Dynamic (Note 5) | | | | | | |
| Total Gate Charge | $V_{DS} = 10V, I_D = 250mA,$ $V_{GS} = 4.5V$ | Q_g | | 0.4 | 0.6 | nC |
| Input Capacitance | $V_{DS} = 25V, V_{GS} = 0V,$ | C _{iss} | | 30 | | |
| Output Capacitance | | C _{oss} | | 6 | | pF |
| Reverse Transfer Capacitance | f = 1.0MHz | C _{rss} | | 2.5 | | - |
| Gate Resistance | F = 1MHz, open drain | R_{g} | | 70 | | Ω |
| Switching (Note 6) | | | | | | |
| Turn-On Delay Time | $V_{DD} = 30V, R_G = 10\Omega$ $t_{d(on)}$ | | 25 | | | |
| Turn-Off Delay Time | $I_D = 200 \text{mA}, V_{GEN} = 10 \text{V},$ | t _{d(off)} | | 35 | | ns |
| Source-Drain Diode (Note 4) | | | | | | |
| Diode Forward Voltage | I _S =300mA, V _{GS} =0V | V_{SD} | | 0.8 | 1.4 | |
| Reverse Recovery Time | I _S = 0.5A | t _{rr} | | 40 | | ns |
| Reverse Recovery Charge | $dI_F/dt = 100A/\mu s$ | Q_{rr} | | 39 | | nC |

Notes:

- 1. Current limited by package
- 2. Pulse width limited by the maximum junction temperature
- 3. L = 0.1 mH, $I_{AS} = 2A$, $V_{DD} = 25V$, $R_G = 25\Omega$, Starting $T_J = 25^{\circ}C$
- 4. Pulse test: PW \leq 300 μ s, duty cycle \leq 2%
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.

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ORDERING INFORMATION

| PART NO. | PACKAGE | PACKING |
|------------------|---------|--------------------|
| TSM2N7002KCX RFG | SOT-23 | 3,000pcs / 7" Reel |

Note:

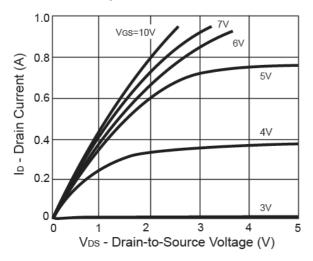
- 1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- 2. Halogen-free according to IEC 61249-2-21 definition



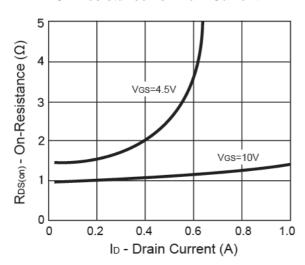
CHARACTERISTICS CURVES

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$

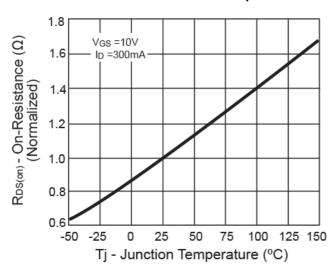
Output Characteristics



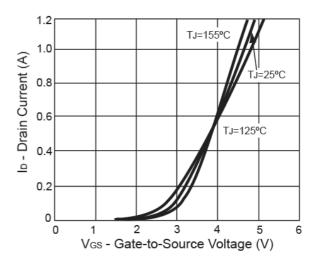
On-Resistance vs. Drain Current



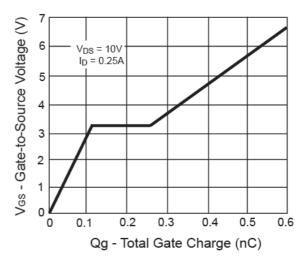
On-Resistance vs. Junction Temperature



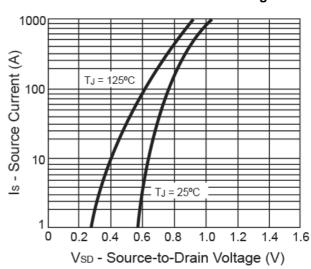
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage

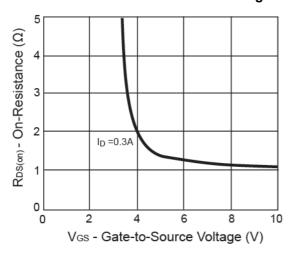




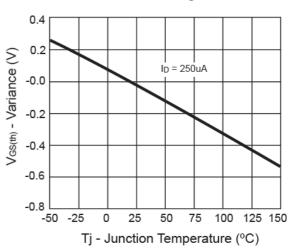
CHARACTERISTICS CURVES

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$

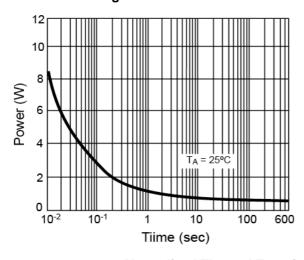
On-Resistance vs. Gate-Source Voltage



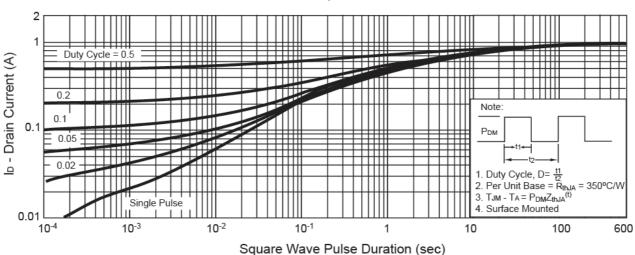
Threshold Voltage



Single Pulse Power

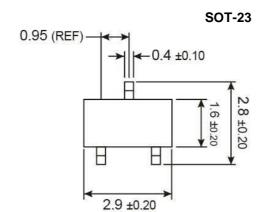


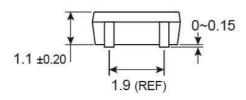
Normalized Thermal Transient Impedance, Junction-to-Ambient

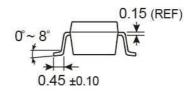




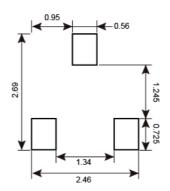
PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)





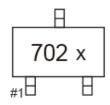


SUGGESTED PAD LAYOUT (Unit: Millimeters)



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MARKING DIAGRAM



702 = TSM2N7002KCX Device Code

X = Internal Code



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